

## Phase Control Thyristor

### Types N1467NS200 to N1467NS260

#### Absolute Maximum Ratings

	VOLTAGE RATINGS	MAXIMUM LIMITS	UNITS
$V_{DRM}$	Repetitive peak off-state voltage, (note 1)	2000-2600	V
$V_{DSM}$	Non-repetitive peak off-state voltage, (note 1)	2000-2600	V
$V_{RRM}$	Repetitive peak reverse voltage, (note 1)	2000-2600	V
$V_{RSM}$	Non-repetitive peak reverse voltage, (note 1)	2100-2700	V

	OTHER RATINGS	MAXIMUM LIMITS	UNITS
$I_{T(AV)}$	Mean on-state current, $T_{sink}=55^{\circ}C$ , (note 2)	1467	A
$I_{T(AV)}$	Mean on-state current, $T_{sink}=85^{\circ}C$ , (note 2)	997	A
$I_{T(AV)}$	Mean on-state current, $T_{sink}=85^{\circ}C$ , (note 3)	595	A
$I_{T(RMS)}$	Nominal RMS on-state current, $25^{\circ}C$ , (note 2)	2912	A
$I_{T(d.c.)}$	D.C. on-state current, $25^{\circ}C$ , (note 4)	2486	A
$I_{TSM}$	Peak non-repetitive surge $t_p=10ms$ , $V_{RM}=0.6V_{RRM}$ , (note 5)	21.5	kA
$I_{TSM2}$	Peak non-repetitive surge $t_p=10ms$ , $V_{RM}\leq 10V$ , (note 5)	23.6	kA
$I^2t$	$I^2t$ capacity for fusing $t_p=10ms$ , $V_{RM}=0.6V_{RRM}$ , (note 5)	$2.31 \times 10^6$	$A^2s$
$I^2t$	$I^2t$ capacity for fusing $t_p=10ms$ , $V_{RM}\leq 10V$ , (note 5)	$2.78 \times 10^6$	$A^2s$
$di/\tau/dt$	Maximum rate of rise of on-state current (repetitive), (Note 6)	500	$A/\mu s$
	Maximum rate of rise of on-state current (non-repetitive), (Note 6)	1000	$A/\mu s$
$V_{RGM}$	Peak reverse gate voltage	5	V
$P_{G(AV)}$	Mean forward gate power	4	W
$P_{GM}$	Peak forward gate power	30	W
$V_{GD}$	Non-trigger gate voltage, (Note 7)	0.25	V
$T_{HS}$	Operating temperature range	-40 to +125	$^{\circ}C$
$T_{stg}$	Storage temperature range	-40 to +150	$^{\circ}C$

#### Notes:-

- 1) De-rating factor of 0.13% per  $^{\circ}C$  is applicable for  $T_j$  below  $25^{\circ}C$ .
- 2) Double side cooled, single phase; 50Hz,  $180^{\circ}$  half-sinewave.
- 3) Single side cooled, single phase; 50Hz,  $180^{\circ}$  half-sinewave.
- 4) Double side cooled.
- 5) Half-sinewave,  $125^{\circ}C T_j$  initial.
- 6)  $V_D=67\% V_{DRM}$ ,  $I_{TM}=1500A$ ,  $I_{FG}=2A$ ,  $t_f\leq 0.5\mu s$ ,  $T_{case}=125^{\circ}C$ .
- 7) Rated  $V_{DRM}$ .

**Characteristics**

	PARAMETER	MIN.	TYP.	MAX.	TEST CONDITIONS (Note 1)	UNITS
$V_{TM}$	Maximum peak on-state voltage	-	-	1.69	$I_{TM}=2550A$	V
$V_0$	Threshold voltage	-	-	1.0		V
$r_s$	Slope resistance	-	-	0.272		$m\Omega$
$dv/dt$	Critical rate of rise of off-state voltage	1000	-	-	$V_D=80\% V_{DRM}$	$V/\mu s$
$I_{DRM}$	Peak off-state current	-	-	100	Rated $V_{DRM}$	mA
$I_{RRM}$	Peak reverse current	-	-	100	Rated $V_{RRM}$	mA
$V_{GT}$	Gate trigger voltage	-	-	3.0	$T_j=25^\circ C$	V
$I_{GT}$	Gate trigger current	-	-	300	$T_j=25^\circ C$ , $V_D=10V$ , $I_T=2A$	mA
$I_H$	Holding current	-	-	1000	$T_j=25^\circ C$	mA
$R_\theta$	Thermal resistance, junction to heatsink	-	-	0.024	Double side cooled	K/W
		-	-	0.048	Single side cooled	K/W
F	Mounting force	19	-	26		kN
$W_t$	Weight	-	510	-		g

Notes:-

1) Unless otherwise indicated  $T_j=125^\circ C$ .

## Notes on Ratings and Characteristics

### 1.0 Voltage Grade Table

Voltage Grade 'H'	$V_{DRM}$ V	$V_{DSM}$ V	$V_{RRM}$ V	$V_{RSM}$ V	$V_D$ DC V	$V_R$ DC V
20	2000			2100		1250
22	2200			2300		1350
24	2400			2500		1450
26	2600			2700		1550

### 2.0 Extension of Voltage Grades

This report is applicable to other and higher voltage grades when supply has been agreed by Sales/Production.

### 3.0 De-rating Factor

A blocking voltage de-rating factor of 0.13%/°C is applicable to this device for  $T_j$  below 25°C.

### 4.0 Repetitive dv/dt

Standard dv/dt is 1000V/μs.

### 5.0 Computer Modelling Parameters

#### 5.1 Device Dissipation Calculations

$$I_{AV} = \frac{-V_0 + \sqrt{V_0^2 + 4 \cdot ff^2 \cdot r_s \cdot W_{AV}}}{2 \cdot ff^2 \cdot r_s} \quad \text{and:} \quad W_{AV} = \frac{\Delta T}{R_{th}}$$

$$\Delta T = T_{j\max} - T_{Hs}$$

Where  $V_0=1.0V$ ,  $r_s=0.272m\Omega$ ,

$R_{th}$  = Supplementary thermal impedance, see table below.

$ff$  = Form factor, see table below.

Supplementary Thermal Impedance							
Conduction Angle	30°	60°	90°	120°	180°	270°	d.c.
Square wave Double Side Cooled	0.0293	0.0285	0.0278	0.0271	0.0261	0.0249	0.024
Square wave Single Side Cooled	0.0534	0.053	0.0524	0.0518	0.0509	0.0497	0.0489
Sine wave Double Side Cooled	0.0286	0.0276	0.0269	0.0263	0.0248		
Sine wave Single Side Cooled	0.0531	0.0523	0.0517	0.0511	0.0497		

Form Factors							
Conduction Angle	30°	60°	90°	120°	180°	270°	d.c.
Square wave	3.46	2.45	2	1.73	1.41	1.15	1
Sine wave	3.98	2.78	2.22	1.88	1.57		

## 5.2 Calculating $V_T$ using ABCD Coefficients

The on-state characteristic  $I_T$  vs.  $V_T$ , on page 7 is represented in two ways;

- (i) the well established  $V_o$  and  $r_s$  tangent used for rating purposes and
- (ii) a set of constants A, B, C, D, forming the coefficients of the representative equation for  $V_T$  in terms of  $I_T$  given below:

$$V_T = A + B \cdot \ln(I_T) + C \cdot I_T + D \cdot \sqrt{I_T}$$

The constants, derived by curve fitting software, are given below for both hot and cold characteristics. The resulting values for  $V_T$  agree with the true device characteristic over a current range, which is limited to that plotted.

25°C Coefficients		125°C Coefficients	
A	0.7129291	A	0.3809341
B	0.06494638	B	0.153339
C	2.185213x10 <sup>-4</sup>	C	3.377227x10 <sup>-4</sup>
D	-0.001796941	D	-0.01204351

## 5.3 D.C. Thermal Impedance Calculation

$$r_t = \sum_{p=1}^{p=n} r_p \cdot \left( 1 - e^{\frac{-t}{\tau_p}} \right)$$

Where  $p = 1$  to  $n$ ,  $n$  is the number of terms in the series and:

$t$  = Duration of heating pulse in seconds.

$r_t$  = Thermal resistance at time  $t$ .

$r_p$  = Amplitude of  $p_{th}$  term.

$\tau_p$  = Time Constant of  $r_{th}$  term.

D.C. Double Side Cooled					
Term	1	2	3	4	5
$r_p$	0.01249139	6.316833x10 <sup>-3</sup>	1.850855x10 <sup>-3</sup>	1.922045x10 <sup>-3</sup>	6.135330x10 <sup>-4</sup>
$\tau_p$	0.8840810	0.1215195	0.03400152	6.742908x10 <sup>-3</sup>	1.326292x10 <sup>-3</sup>

D.C. Single Side Cooled						
Term	1	2	3	4	5	6
$r_p$	0.02919832	4.863568x10 <sup>-3</sup>	3.744798x10 <sup>-3</sup>	6.818034x10 <sup>-3</sup>	2.183558x10 <sup>-3</sup>	1.848294x10 <sup>-3</sup>
$\tau_p$	6.298105	3.286174	0.5359179	0.1186897	0.02404574	3.379476x10 <sup>-3</sup>

**Curves**

Figure 1 - On-state current vs. Power dissipation - Double Side Cooled (Sine wave)

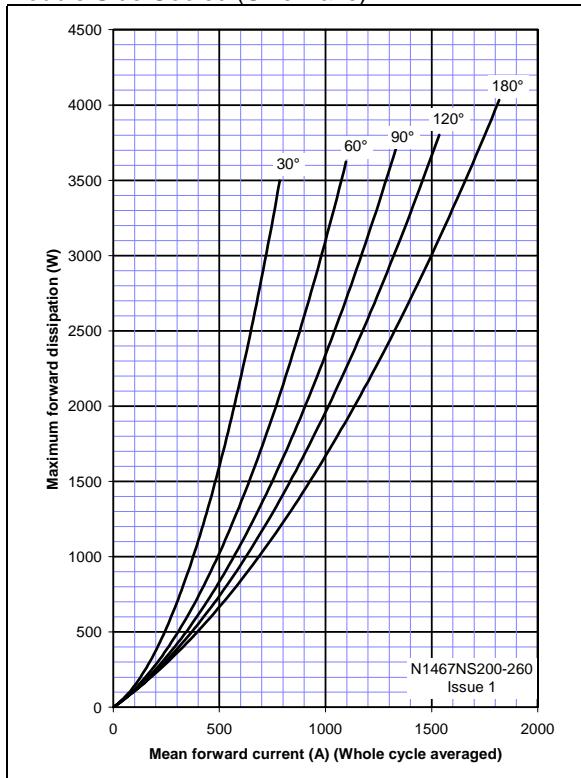


Figure 2 - On-state current vs. Heatsink temperature - Double Side Cooled (Sine wave)

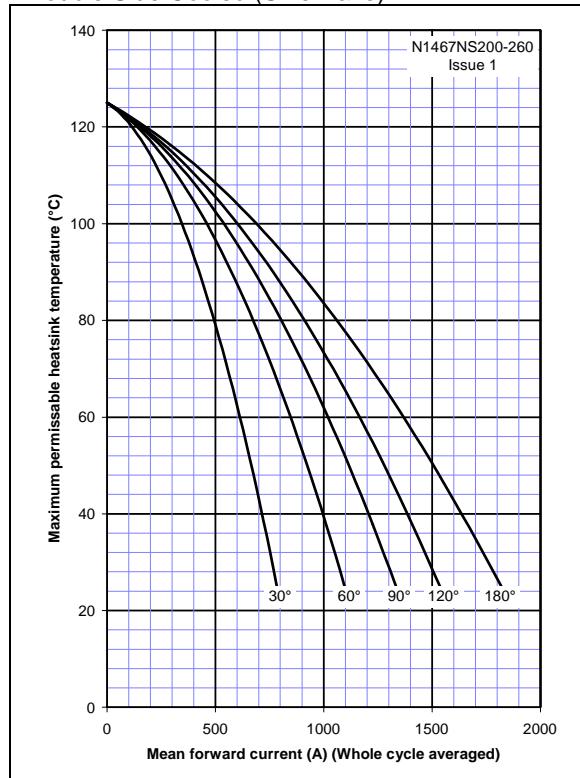


Figure 3 - On-state current vs. Power dissipation - Double Side Cooled (Square wave)

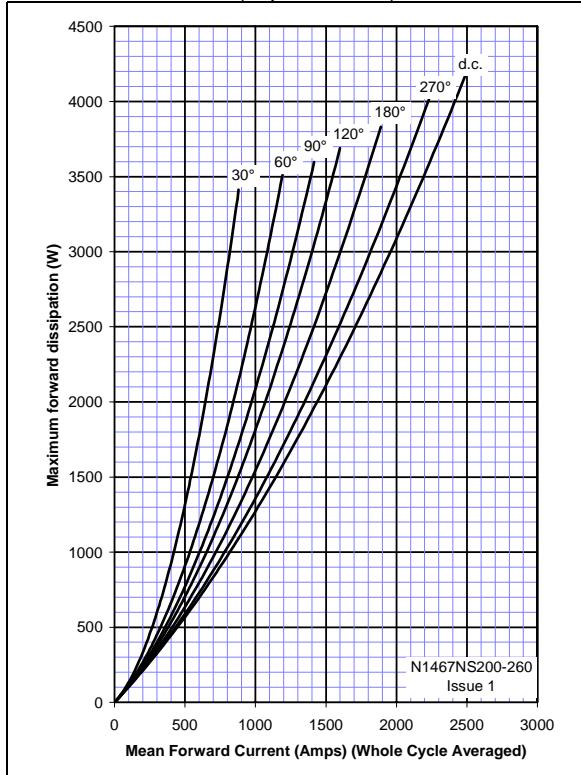


Figure 4 - On-state current vs. Heatsink temperature - Double Side Cooled (Square wave)

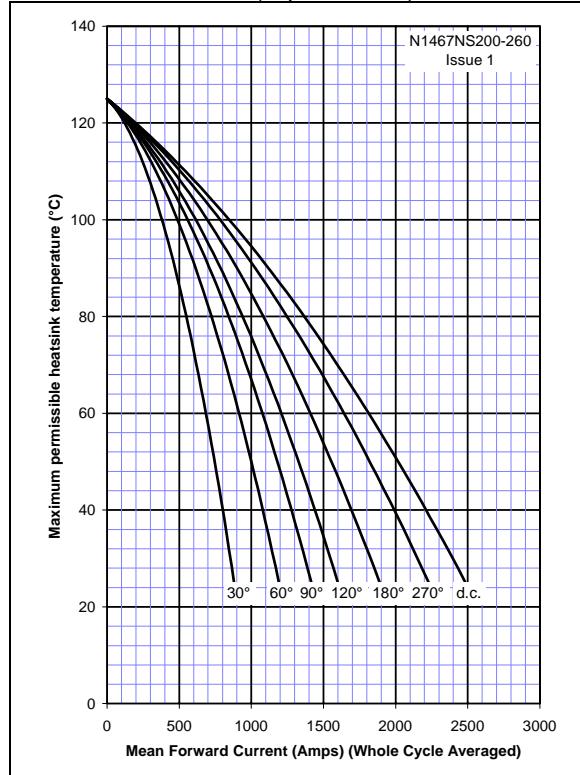


Figure 5 - On-state current vs. Power dissipation - Single Side Cooled (Sine wave)

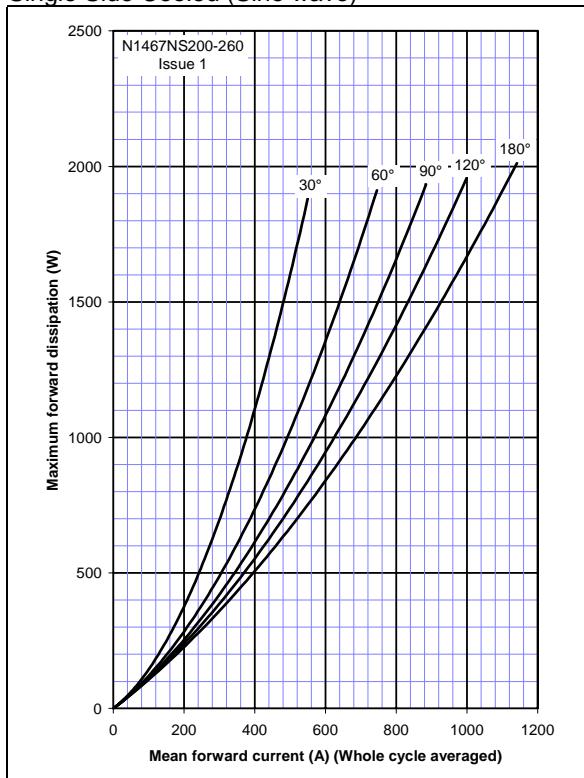


Figure 6 - On-state current vs. Heatsink temperature - Single Side Cooled (Sine wave)

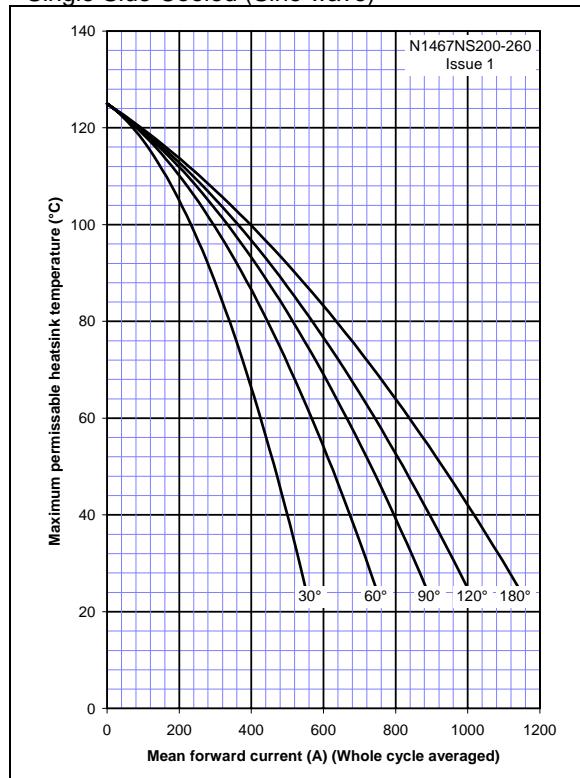


Figure 7 - On-state current vs. Power dissipation - Single Side Cooled (Square wave)

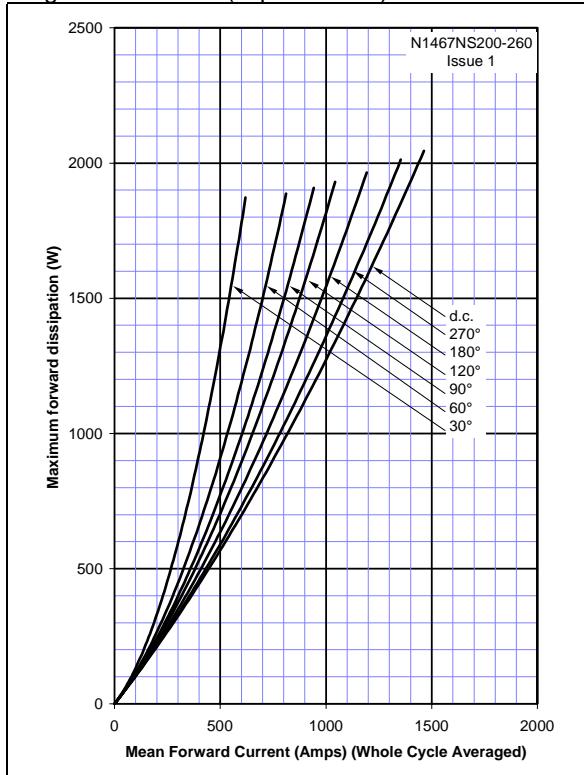


Figure 8 - On-state current vs. Heatsink temperature - Single Side Cooled (Square wave)

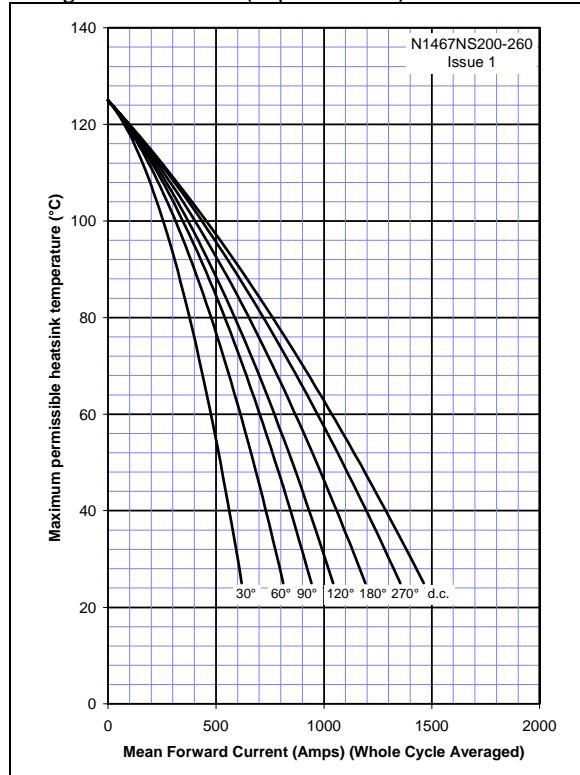


Figure 9 - On-state characteristics of Limit device

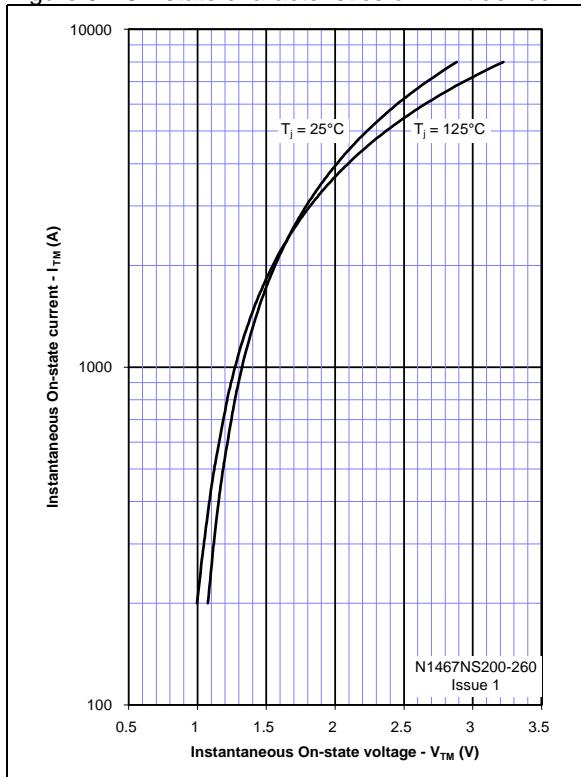


Figure 10 - Transient Thermal Impedance

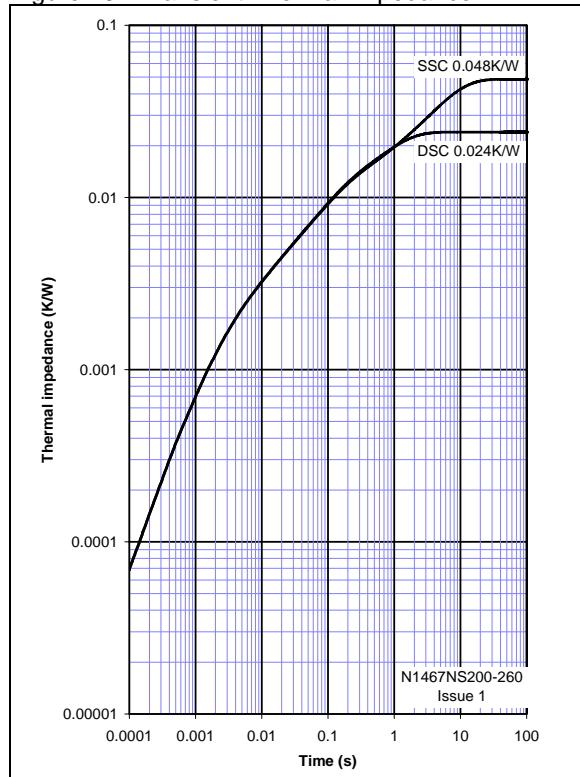


Figure 11 - Gate Characteristics - Trigger Limits

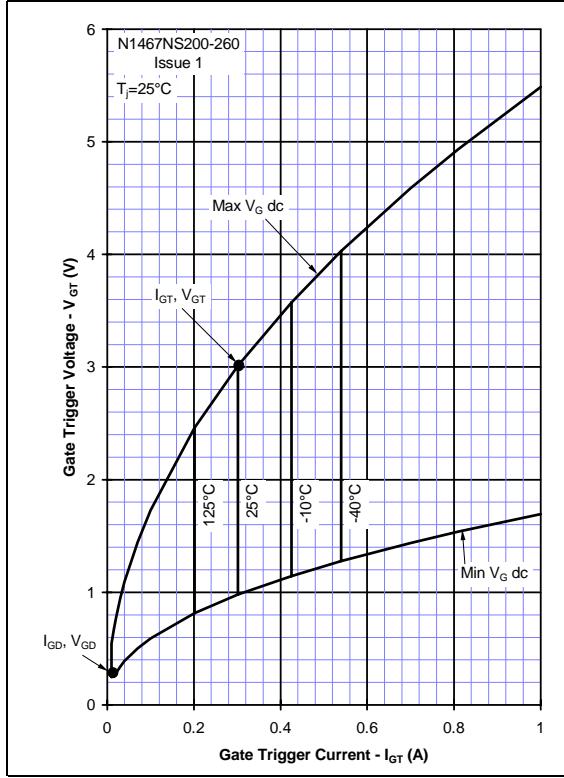


Figure 12 - Gate Characteristics - Power Curves

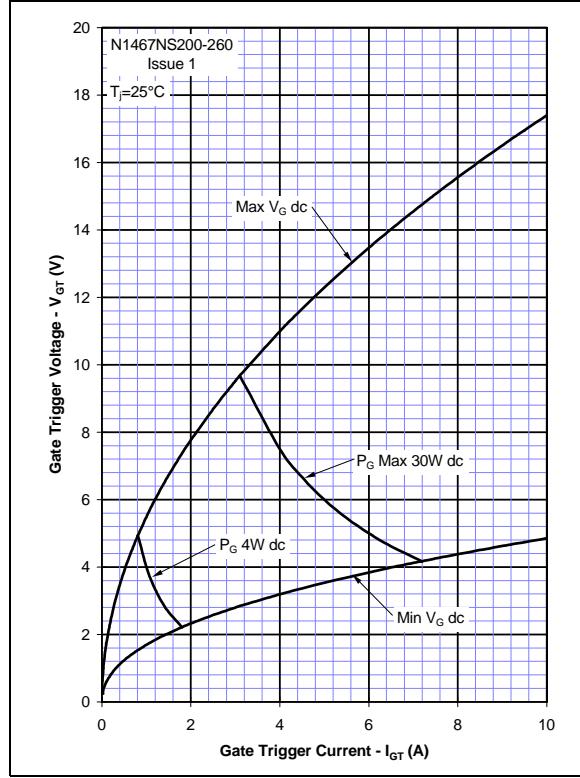
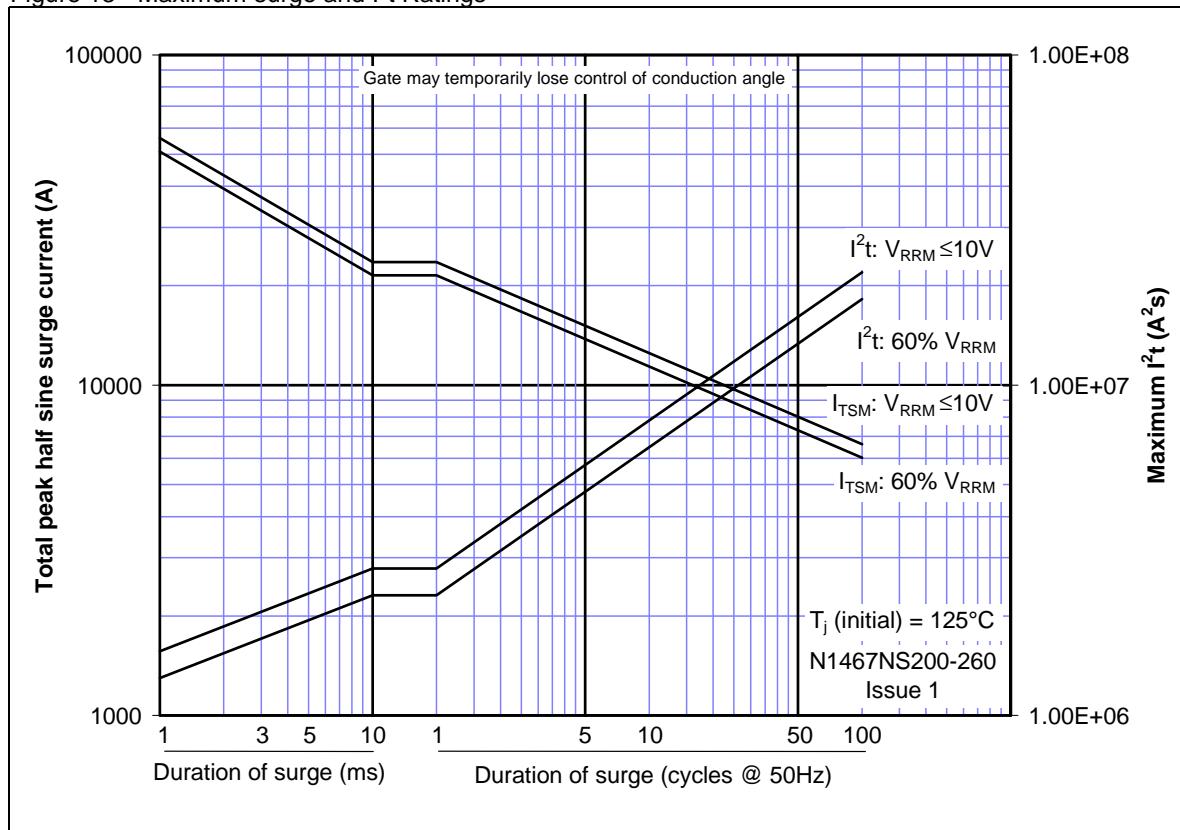


Figure 13 - Maximum surge and  $I^2t$  Ratings

Outline Drawing & Ordering Information